Preferred Devices

General Purpose Transistor

PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 which is designed for low power surface mount applications.

Features

• Pb-Free Package is Available*

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V _{CEO}	-45	V
Collector-Base Voltage	V _{CBO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current – Continuous	I _C	-100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

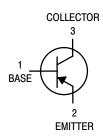
Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T _A = 25°C Derated above 25°C	P _D	200	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T _A = 25°C Derated above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	400	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ min pad.
- 2. FR-4 @ 1.0 × 1.0 in pad.



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CASE 463 SOT-416 STYLE 1

MARKING DIAGRAM



xx = Device Code M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1	l	•	•	I
Collector – Emitter Breakdown Voltage (I _C = -10 mA) BC857 Series	V _{(BR)CEO}	-45	_	_	V
Collector – Emitter Breakdown Voltage $(I_C = -10 \mu A, V_{EB} = 0)$ BC857B Only	V _(BR) CES	-50	_	-	V
Collector – Base Breakdown Voltage ($I_C = -10 \mu A$) BC857 Series	V _{(BR)CBO}	-50	_	-	V
Emitter – Base Breakdown Voltage $(I_E = -1.0 \mu A)$ BC857 Series	V _{(BR)EBO}	-5.0	_	-	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$)	I _{CBO}	- -	_ _	-15 -4.0	nA μA
ON CHARACTERISTICS			•	•	
DC Current Gain $(I_C = -10 \ \mu\text{A}, \ V_{CE} = -5.0 \ \text{V}) \qquad \begin{array}{c} \text{BC857B} \\ \text{BC857C} \end{array}$	h _{FE}	_ _	150 270	- -	-
$(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ BC857B BC857C		220 420	290 520	475 800	
Collector – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA)	V _{CE(sat)}	_ _	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA)	V _{BE(sat)}	_ _	-0.7 -0.9	- -	V
Base – Emitter On Voltage ($I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ($I_C = -10$ mA, $V_{CE} = -5.0$ V)	V _{BE(on)}	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS	<u> </u>				•
Current – Gain – Bandwidth Product ($I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	100	_	-	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{ob}	-	_	4.5	pF
Noise Figure $ (I_C = -0.2 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, \\ f = 1.0 \text{ kHz}, BW = 200 \text{ Hz}) $	NF	-	-	10	dB

TYPICAL CHARACTERISTICS

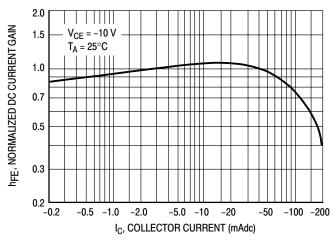


Figure 1. Normalized DC Current Gain

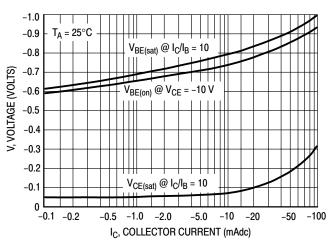


Figure 2. "Saturation" and "On" Voltages

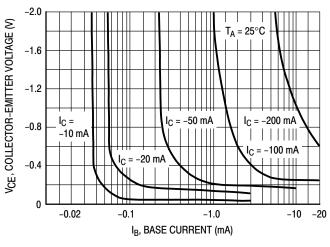


Figure 3. Collector Saturation Region

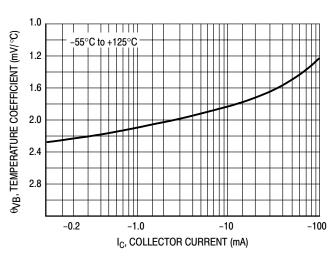


Figure 4. Base-Emitter Temperature Coefficient

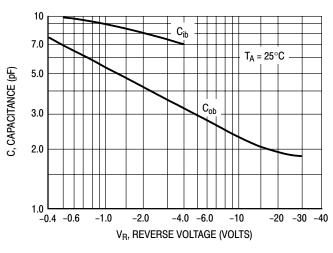


Figure 5. Capacitances

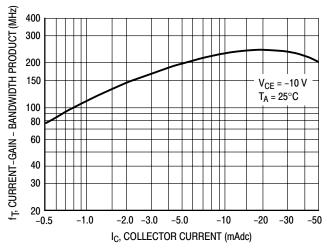


Figure 6. Current-Gain - Bandwidth Product

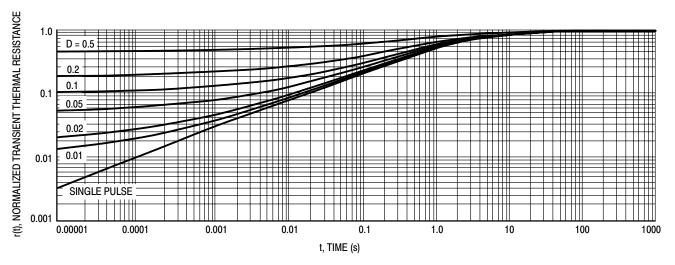


Figure 7. Thermal Response

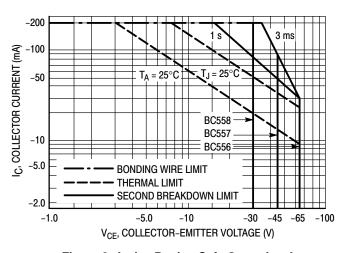


Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 8 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 7. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

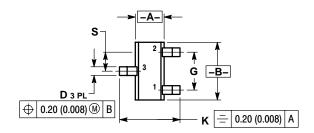
ORDERING INFORMATION

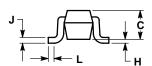
Device	Marking	Package	Shipping [†]
BC857BTT1	3F	SOT-416	
BC857BTT1G	3F	SOT-416 (PB-Free)	3,000 / Tape & Reel
BC857CTT1	3G	SOT-416	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-416 (SC-75) CASE 463-01 ISSUE C





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.70	0.90	0.028	0.035	
В	1.40	1.80	0.055	0.071	
С	0.60	0.90	0.024	0.035	
D	0.15	0.30	0.006	0.012	
G	1.00 BSC		0.039 BSC		
Н	-	0.10	-	0.004	
J	0.10	0.25	0.004	0.010	
K	1.45	1.75	0.057	0.069	
L	0.10	0.20	0.004	0.008	
S	0.50 BSC		0.020	BSC	

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